

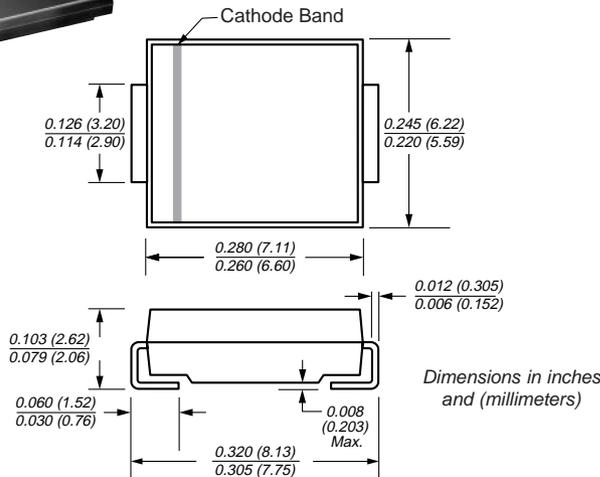


## Ultrafast Rectifiers

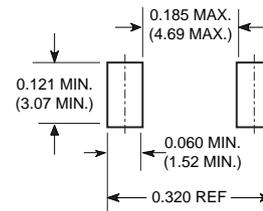
**Reverse Voltage** 400 to 600V  
**Forward Current** 3.0A  
**Reverse Recovery Time** 50ns



DO-214AB (SMC)



### Mounting Pad Layout



### Mechanical Data

**Case:** JEDEC DO-214AB molded plastic body over passivated chip

**Terminals:** Solder plated, solderable per MIL-STD-750, Method 2026

**Polarity:** Color band denotes cathode end

**Weight:** 0.007oz., 0.21g

### Features

- Plastic package has Underwriters Laboratories Flammability Classification 94V-0
- Ideally suited for use in very high frequency switching power supplies, inverters and as free wheeling diodes
- Ultrafast recovery time for high efficiency
- Glass passivated junction
- High temperature soldering guaranteed: 250°C/10 seconds, 0.375" (9.5mm) lead length, 5 lbs. (2.3kg) tension

### Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	MURS340	MURS360	Unit
Device Marking Codes		MG	MJ	
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	400	600	V
Working peak reverse voltage	V <sub>RWM</sub>	400	600	V
Maximum DC blocking voltage	V <sub>DC</sub>	400	600	V
Maximum average forward rectified current at: (See figure 1) $T_L = 130^\circ\text{C}$ $T_L = 115^\circ\text{C}$	I <sub>F(AV)</sub>	3.0 4.0		A
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load (JEDEC Method)	I <sub>FSM</sub>	125		A
Typical thermal resistance junction to ambient	R <sub>θJL</sub>	11		°C/W
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +175°C		°C

### Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Maximum instantaneous forward voltage <sup>(1)</sup>	$I_F = 3.0\text{A}, T_J = 25^\circ\text{C}$ $I_F = 4.0\text{A}, T_J = 25^\circ\text{C}$ $I_F = 3.0\text{A}, T_J = 150^\circ\text{C}$	V <sub>F</sub>	1.25 1.28 1.05	V
Maximum instantaneous reverse current at rated DC blocking voltage <sup>(1)</sup>	$T_J = 25^\circ\text{C}$ $T_J = 150^\circ\text{C}$	I <sub>R</sub>	10 250	μA
Maximum reverse recovery time at I <sub>F</sub> =0.5A, I <sub>R</sub> =1.0A, I <sub>rr</sub> =0.25A		t <sub>rr</sub>	50	ns
Maximum reverse recovery time at, I <sub>F</sub> =1.0A, di/dt=50A/μs, V <sub>R</sub> =30V, I <sub>rr</sub> =10% I <sub>RM</sub>		t <sub>rr</sub>	75	ns
Maximum forward recovery time I <sub>F</sub> =1.0A, di/dt=100A/μs, Rec. to 1.0V		t <sub>fr</sub>	25	ns

**Note:** (1) Pulse test: t<sub>p</sub> = 300μs, duty cycle ≤ 2%

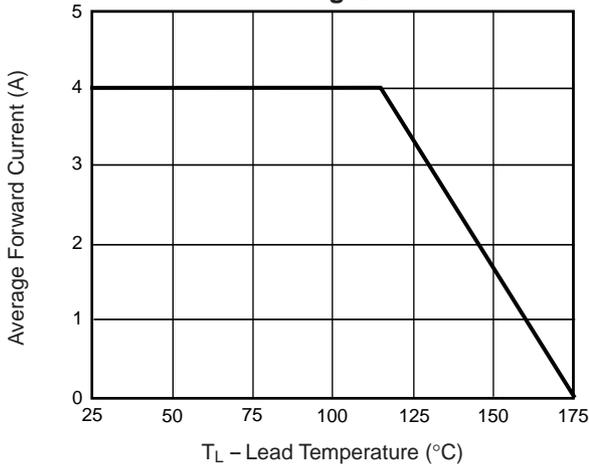
# MURS340 thru MURS360



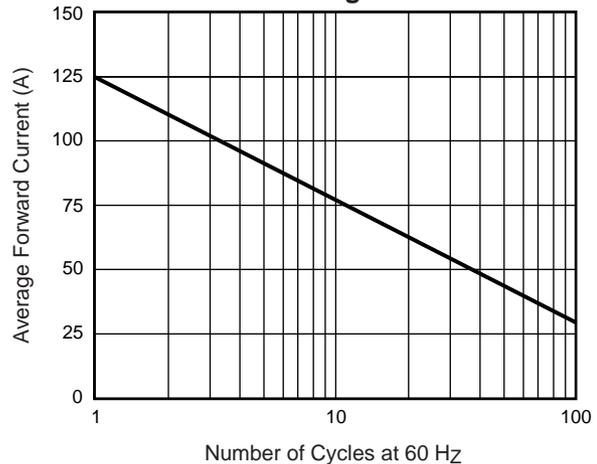
Vishay Semiconductors  
formerly General Semiconductor

## Ratings and Characteristic Curves ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

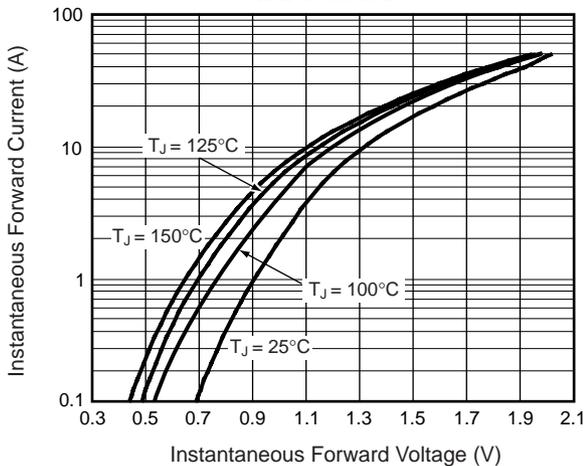
**Fig. 1 – Forward Current Derating Curve**



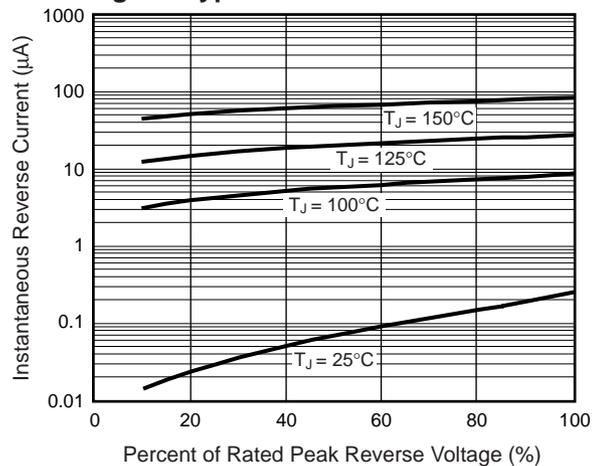
**Fig. 2 – Maximum Non-Repetitive Peak Forward Surge Current**



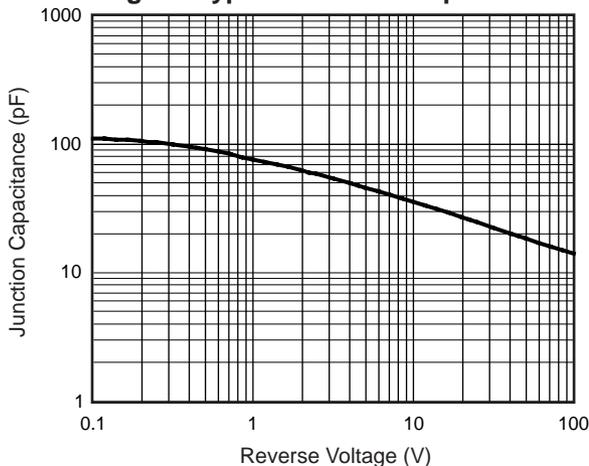
**Fig. 3 – Typical Instantaneous Forward Characteristics**



**Fig. 4 – Typical Reverse Characteristics**



**Fig. 5 – Typical Junction Capacitance**



**Fig. 6 – Typical Reverse Switching Characteristics**

